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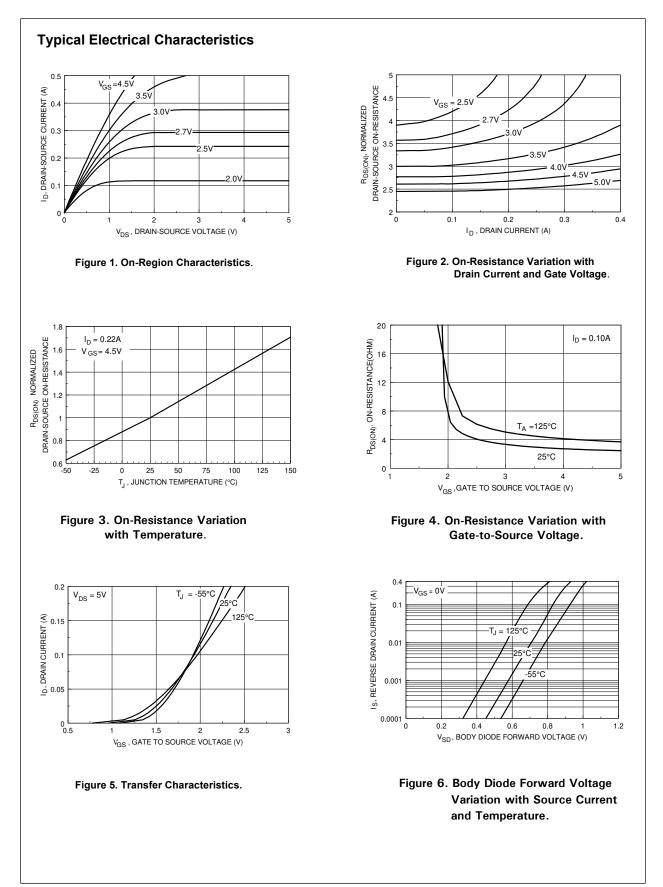
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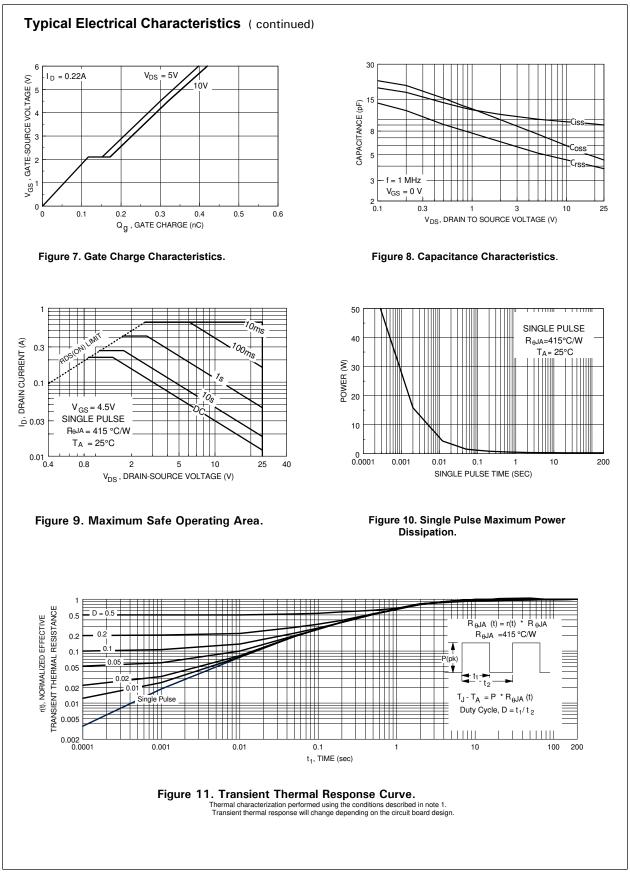
	IRCHILE					July 1999
-	6301N N-Channel, [	Digital FET				
General Description These dual N-Channel logic level enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs.			<ul> <li>Features</li> <li>25 V, 0.22 A continuous, 0.65 A peak.</li></ul>			
ÿ	•			BEBG BEBG		
SC7	0-6 5	OT-23 Su	uperSOT <sup>™</sup> -6	SuperSOT <sup>™</sup> -8	SO-8	SOT-223
	G: D1	.01 G1	D2		2 or 5	6 or 3
Units ins	D1 SC70-6 outs are symmetrical; pin side the carrier can be of e ute Maximum F	1 and 4 are interchan ither orientation and	geable. will not affect the fu		2 or 5 3 or 6	5 or 2 4 or 1 *
Units ins Absol	D1 SC70-6 buts are symmetrical; pin ide the carrier can be of e ute Maximum F Parameter	1 and 4 are interchan ither orientation and $T_A = 24$	geable. will not affect the fu		2 or 5 3 or 6	5 or 2 4 or 1 *
Units ins Absol Symbol	D1 SC70-6 buts are symmetrical; pin side the carrier can be of e ute Maximum F Parameter Drain-Source Voltag	1 and 4 are interchan ither orientation and <b>Ratings</b> $T_A = 2t$	geable. will not affect the fu		2 or 5 3 or 6 FDG6301N 25	5 or 2 4 or 1 *
Units ins Absol Symbol / <sub>DSS</sub> / <sub>GSS</sub>	D1 SC70-6 buts are symmetrical; pin ide the carrier can be of e ute Maximum F Parameter	1 and 4 are interchan ither orientation and $T_A = 23$	geable. will not affect the fu 5°C unless otherw		2 or 5 3 or 6 <b>FDG6301N</b> 25 8 0.22	5 or 2 4 or 1 *
Units ins	D1 SC70-6 outs are symmetrical; pin side the carrier can be of e ute Maximum F Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Curren	$T_{A} = 2$ $T_{A} = 2$ $T_{A} = 2$ $T_{A} = 2$	geable. will not affect the fu 5°C unless otherw		2 or 5 3 or 6 FDG6301N 25 8 0.22 0.65	5 or 2 4 or 1 * Units V V A
Units ins Absol Symbol /DSS /GSS D D D	D1 SC70-6 suts are symmetrical; pin side the carrier can be of e ute Maximum F Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Curren Maximum Power Dis	1 and 4 are interchan ither orientation and the Ratings $T_A = 2t$ e e t - Continuous - Pulsed ssipation	geable. will not affect the fu 5°C unless otherw		2 or 5 3 or 6 <b>FDG6301N</b> 25 8 0.22 0.65 0.3	5 or 2 4 or 1 * Units V V
Units ins Absol Symbol / <sub>DSS</sub> / <sub>GSS</sub> D C D C D T <sub>J</sub> ,T <sub>STG</sub>	D1 SC70-6 outs are symmetrical; pin side the carrier can be of e ute Maximum F Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Curren	1 and 4 are interchan ither orientation and $r_A = 23$ e e t - Continuous - Pulsed ssipation ge Temperature R- ge Rating MIL-ST	geable. will not affect the fur 5°C unless otherw (Note 1) ange		2 or 5 3 or 6 FDG6301N 25 8 0.22 0.65	5 or 2 4 or 1 * V V V A W
Units ins Absol Symbol V <sub>DSS</sub> V <sub>GSS</sub> b C C C C C C C C C C C C C	D1 SC70-6 outs are symmetrical; pin side the carrier can be of e ute Maximum F Parameter Drain-Source Voltage Gate-Source Voltage Drain/Output Curren Maximum Power Dis Operating and Stora Electrostatic Dischar	1 and 4 are interchan ither orientation and 1 Ratings $T_A = 22$ e e t - Continuous - Pulsed ssipation ge Temperature R- ge Rating MIL-ST (100 pF / 1500 $\Omega$ )	geable. will not affect the fur 5°C unless otherw (Note 1) ange		2 or 5         3 or 6 <b>FDG6301N</b> 25         8         0.22         0.65         0.3         -55 to 150	5 or 2 5 or 2 4 or 1 * V V V V A W °C

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS	· ·				•
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	25			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25 \ ^\circ\text{C}$		25		mV /°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 20 \text{ V}, \ V_{GS} = 0 \text{ V}$			1	μA
		$T_{J} = 55^{\circ}C$			10	μA
I <sub>GSS</sub>	Gate - Body Leakage Current	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
ON CHARA	CTERISTICS (Note 2)	•				•
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = 250 \ \mu\text{A}$	0.65	0.85	1.5	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate Threshold Voltage Temp.Coefficient	$I_D = 250 \ \mu\text{A}$ , Referenced to $25 \ ^\circ\text{C}$		-2.1		mV /°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, \ \text{I}_{D} = 0.22 \text{ A}$		2.6	4	Ω
. ,		T <sub>J</sub> =125°C		5.3	7	
		$V_{GS} = 2.7 \text{ V}, \ I_{D} = 0.19 \text{ A}$		3.7	5	
I <sub>D(ON)</sub>	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	0.22			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{\rm DS} = 5 \text{ V}, \ \text{I}_{\rm D} = \ 0.22 \text{ A}$		0.2		S
DYNAMIC C	HARACTERISTICS					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ f = 1.0 MHz		9.5		pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		6		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			1.3		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 5 V, I_D = 0.5 A,$		5	10	ns
t,	Turn - On Rise Time	$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 50 \Omega$		4.5	10	ns
t <sub>D(off)</sub>	Turn - Off Delay Time			4	8	ns
t <sub>r</sub>	Turn - Off Fall Time			3.2	7	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 5 V, I_D = 0.22 A,$ $V_{GS} = 4.5 V$		0.29	0.4	nC
Q <sub>gs</sub>	Gate-Source Charge	$v_{GS} = 4.5 v$		0.12		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.03		nC
	RCE DIODE CHARACTERISTICS AND MAXIM	IUM RATINGS	r	1	1	
I <sub>s</sub>	Maximum Continuous Source Current				0.25	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \ V, \ I_S = 0.25 \ A \ (\text{Note 2})$		0.8	1.2	V

Notes:

1. R<sub>pk</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>pkc</sub> is guaranteed  $r_{g_{WA}}$  by design while  $R_{g_{WA}}$  is determined by the user's board design.  $R_{g_{WA}} = 415^{\circ}C/W$  on minimum pad mounting on FR-4 board in still air. 2. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%.





FDG6301N Rev.E1

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